

1N6100

Isolated Diode Array with HiRel MQ, MX, MV, and MSP Screening Options

DESCRIPTION

These low capacitance diode arrays are multiple, discrete, isolated junctions fabricated by a planar process and mounted in a 14-PIN package for use as steering diodes protecting up to seven I/O ports from ESD, EFT, or surge by directing them either to the positive side of the power supply line or to ground (see figure 1). An external TVS diode may be added between the positive supply line and ground to prevent overvoltage on the supply rail. They may also be used in fast switching coredriver applications. This includes computers and peripheral equipment such as magnetic cores, thin-film memories, plated-wire memories, etc., as well as decoding or encoding applications. These arrays offer many advantages of integrated circuits such as high-density packaging and improved reliability. This is a result of fewer pick and place operations, smaller footprint, smaller weight, and elimination of various discrete packages that may not be as user friendly in PC board mounting.

APPEARANCE



14-PIN Ceramic Flat Pack

IMPORTANT: For the most current data, consult *MICROSEMI's* website: http://www.microsemi.com

FEATURES

- Hermetic Ceramic Package ٠
- Isolated Diodes to Eliminate Cross-Talk Voltages High Breakdown Voltage V_{BR} > 75 V at 5 μ A •
- Low Leakage I_R< 100 nA at 40 V •
- Low Capacitance C < 4.0 pF ٠
- Switching Speeds less than 10 ns
- Options for screening in accordance with MIL-PRF-19500/474 for JAN, JANTX, JANTXV, and JANS are available by adding MQ, MX, MV, or MSP prefixes respectively to part numbers. For example, designate MX1N6100 for a JANTX screen.

MAXIMUM RATINGS

- Reverse Breakdown Voltage of 75 Vdc (Note 1 & 2) •
- Continuous Forward Current of 300 mA dc (Note 1 & 3) •
- Peak Surge Current (tp=1/120 s) of 500 mA dc (Note 1) .
- 400 mW Power Dissipation per Junction @ 25°C .
- 500 mW Power Dissipation per Package @ 25°C (Note 4) •
- Operating Junction Temperature range -65 to +150°C .
- Storage Temperature range of -65 to +200°C
- NOTE 1: Each Diode NOTE 2: Pulsed: P_W = 100 ms max; duty cycle <20%
 - NOTE 3: Derate at 2.4 mA/°C above +25°C
 - NOTE 4: Derate at 4.0 mW/°C above +25°C

61000-4-5 (surge): 12 A, 8/20 µs **MECHANICAL AND PACKAGING**

APPLICATIONS / BENEFITS

RS-232 & RS-422 Interface Networks

IEC 61000-4 Compatible (See Circuit in

61000-4-4 (EFT): 40 A - 5/50 ns

61000-4-2 (ESD): Air 15 kV, contact - 8 kV

High Frequency Data Lines

Ethernet: 10 Base T

Computer I/O Ports

Switching Core Drivers

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LAN

Figure 1)

- 14-PIN Ceramic Flat Pack
- Weight 0.29 grams (approximate)
- Marking: Logo, part number, date code and dot identifying pin #1
- Carrier Tubes; 19 pcs (standard)

ELECTRICAL CHARACTERISTICS (Per Diode) @ 25°C unless otherwise specified							
	MAXIMUM FORWARD VOLTAGE V _{F1}	MAXIMUM REVERSE CURRENT	MAXIMUM REVERSE CURRENT	MAXIMUM CAPACITANCE (PIN TO PIN) Ct	MAXIMUM FORWARD RECOVERY TIME	$\begin{tabular}{l} MAXIMUM \\ REVERSE \\ RECOVERY TIME \\ trr \\ I_F = I_R = 10 \mbox{ mAdc} \end{tabular}$	MAXIMUM FORWARD VOLTAGE MATCH
	I _F = 100 mA	I _{R1}	I _{R2}	$V_R = 0 V$	t _{fr}	i _{rr} = 1 mAdc	V _{F5}
PART	(Note 1)	$V_R = 40 V$	$V_R = 20 V$	F = 1 MHz	I _F = 100 mA	R _L = 100 ohms	I _F = 10 mA
NUMBE	ER V	μA	nA	pF	ns	ns	mV
1N6100) 1	0.1	25	4.0	15	10	5

NOTE 1: Pulsed: $P_W = 300 \ \mu s \ +/-50 \ \mu s$, duty cycle <2%, 90 μs after leading edge.



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BL

BW₂

Max

9.91

6.60

2.41

9.40

1.14

0.15

7.11

0.48